60V 175°C N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	Q_G Typ	I_D Max T_C = +25°C (Note 9)
60V	3.8mΩ @ V_{GS} = 10V	95.4nC	100A

Features

- Rated to +175°C – Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching – Ensures More Reliable and Robust End Application
- Low $R_{DS(ON)}$ – Minimizes Power Losses
- Low Q_G – Minimizes Switching Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMTH6004SK3Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**
  https://www.diodes.com/quality/product-definitions/

Description and Applications

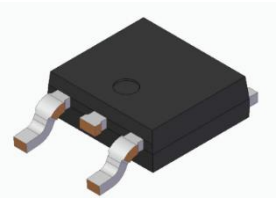
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Engine management systems
- Body control electronics
- DC-DC converters
- Motor control

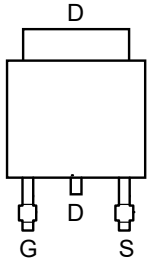
Mechanical Data

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.33 grams (Approximate)

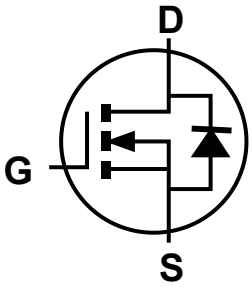
TO252 (DPAK)



Top View



Top View Pinout



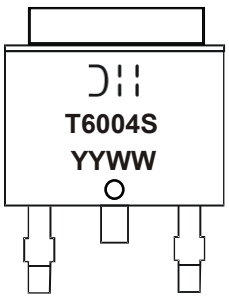
Internal Schematic

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMTH6004SK3Q-13	TO252 (DPAK)	2,500	Tape & Reel

Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



=Manufacturer's Marking
T6004S = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 26 = 2026)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current (Note 6)	T_C = +25°C (Note 9) T_C = +100°C	I_D	100 75	A
Maximum Body Diode Forward Current (Note 6)	T_C = +25°C	I_S	100	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I_{DM}	150	A
Avalanche Current, L = 0.2mH		I_{AS}	45	A
Avalanche Energy, L = 0.2mH		E_{AS}	200	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	3.9	W
Thermal Resistance, Junction to Ambient (Note 5)		$R_{\theta JA}$	38	°C/W
Total Power Dissipation (Note 6	T_C = +25°C	P_D	180	W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	0.8	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +175	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	V_{GS} = 0, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS} = 48V, V_{GS} = 0
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	2	—	4	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3	3.8	mΩ	V_{GS} = 10V, I_D = 90A
Diode Forward Voltage	V_{SD}	—	0.9	1.2	V	V_{GS} = 0, I_S = 20A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{ISS}	—	4,556	—	pF	V_{DS} = 30V, V_{GS} = 0, f = 1MHz
Output Capacitance	C_{OSS}	—	1,383	—		
Reverse Transfer Capacitance	C_{RSS}	—	105.2	—		
Gate Resistance	R_G	—	0.66	—	Ω	V_{DS} = 0, V_{GS} = 0, f = 1MHz
Total Gate Charge	Q_G	—	95.4	—	nC	V_{DS} = 30V, I_D = 90A, V_{GS} = 10V
Gate-Source Charge	Q_{GS}	—	21.6	—		
Gate-Drain Charge	Q_{GD}	—	20.4	—		
Turn-On Delay Time	$t_{D(ON)}$	—	13.2	—	ns	V_{DD} = 30V, V_{GS} = 10V, I_D = 90A, R_G = 3.5Ω
Turn-On Rise Time	t_R	—	11.7	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	31	—		
Turn-Off Fall Time	t_F	—	12	—		
Body Diode Reverse-Recovery Time	t_{RR}	—	50.5	—	ns	I_F = 50A, di/dt = 100A/µs
Body Diode Reverse-Recovery Charge	Q_{RR}	—	80.8	—	nC	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout.
6. Thermal resistance from junction to soldering point (on the exposed drain pad).
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to production testing.
9. Package limited.

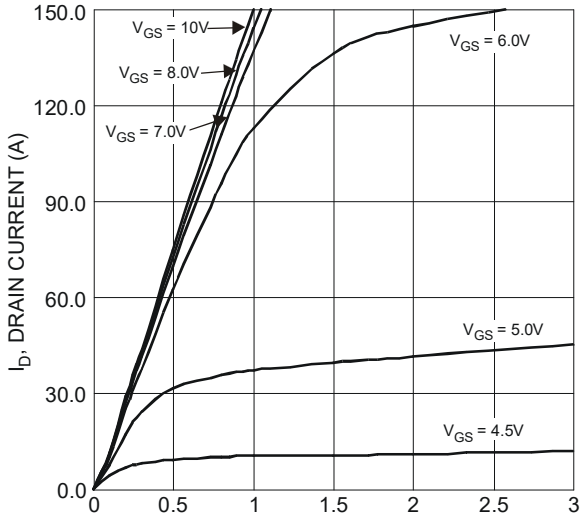


Figure 1 Typical Output Characteristics

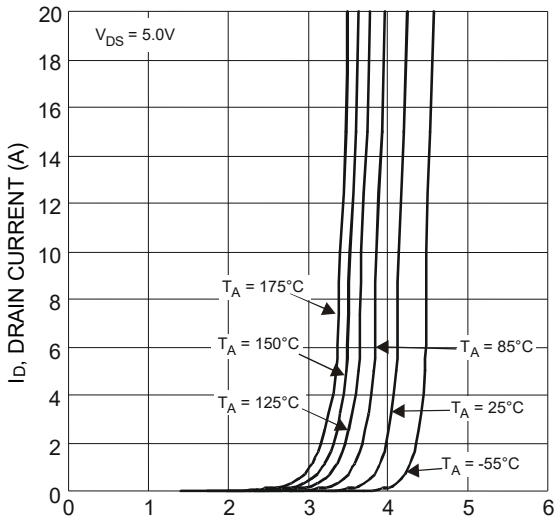


Figure 2 Typical Transfer Characteristics

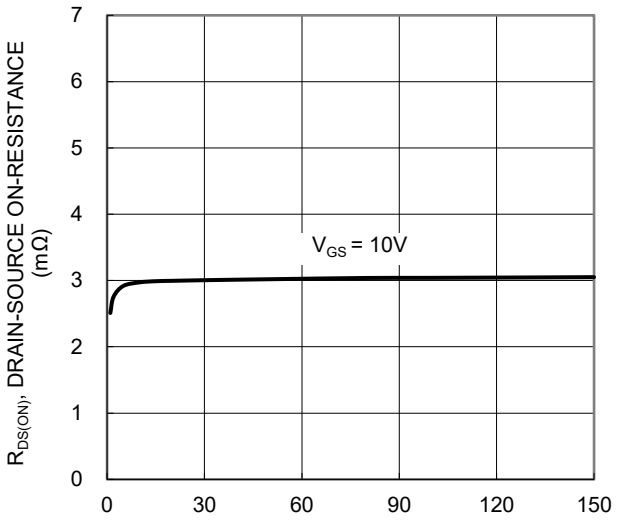


Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage

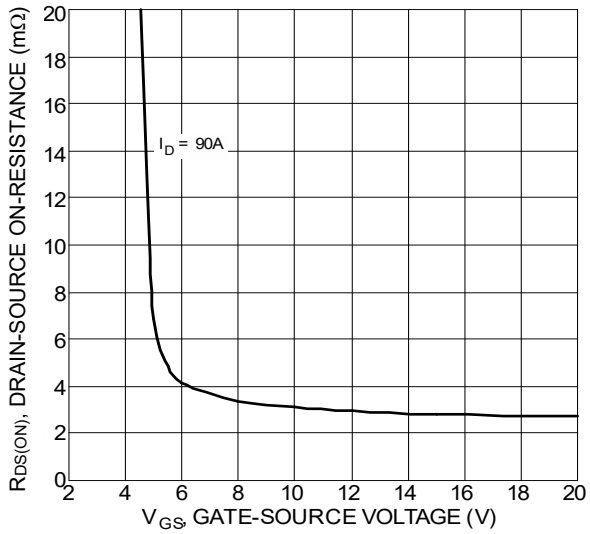


Figure 4 Typical Drain-Source On-Resistance vs. Gate-Source Voltage

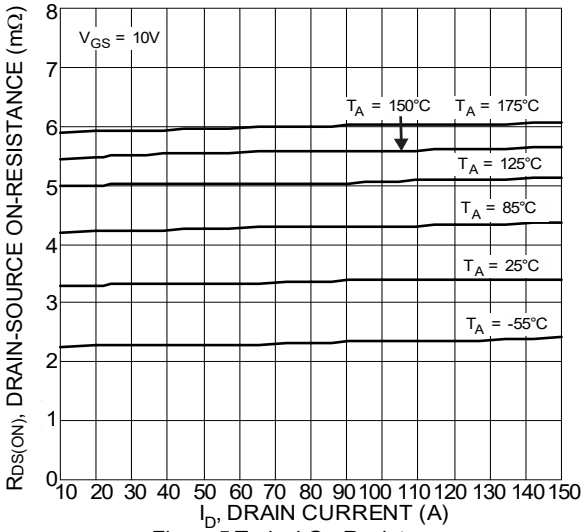


Figure 5 Typical On-Resistance vs. Drain Current and Temperature

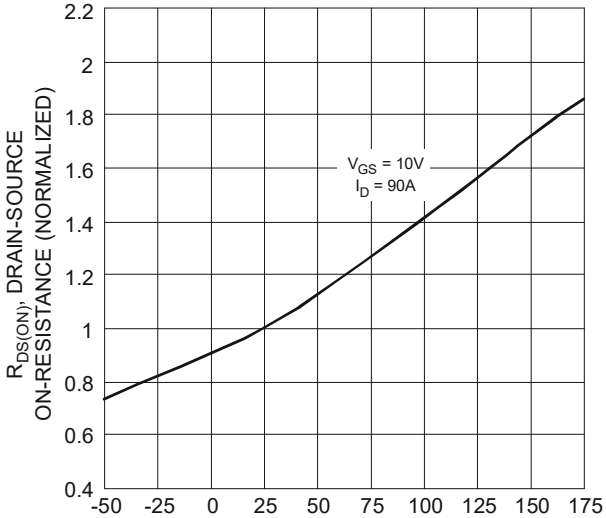


Figure 6 On-Resistance Variation with Temperature

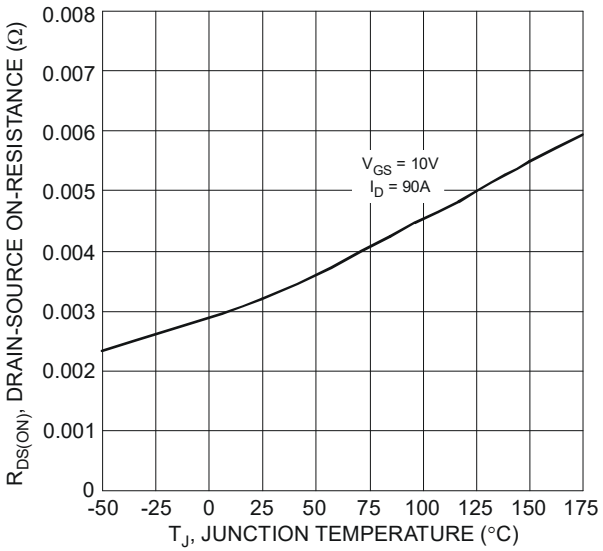


Figure 7 On-Resistance Variation with Temperature

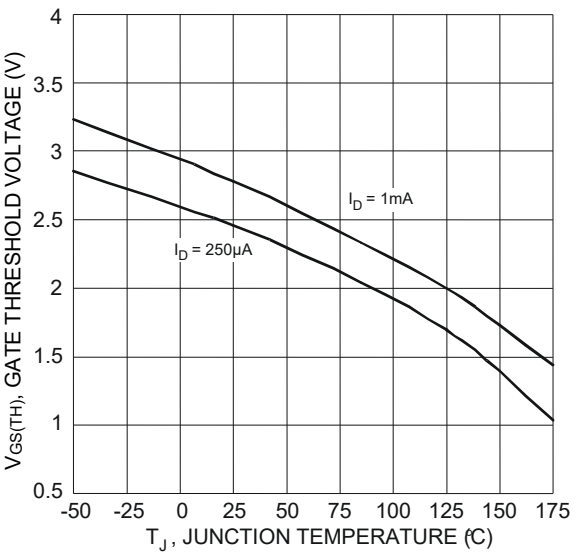


Figure 8 Gate Threshold Variation vs. Temperature

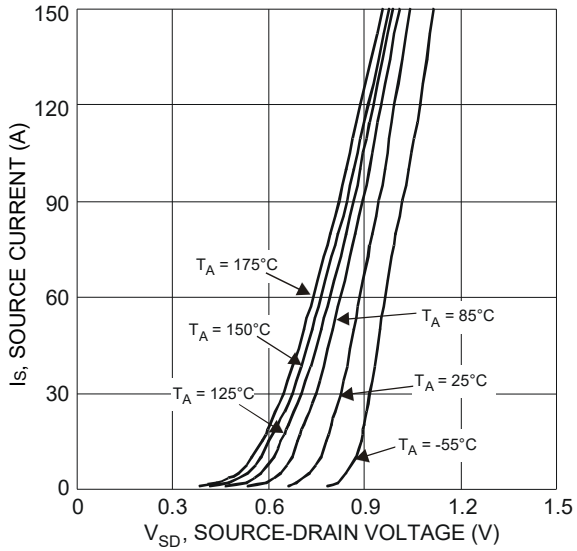


Figure 9 Diode Forward Voltage vs. Current

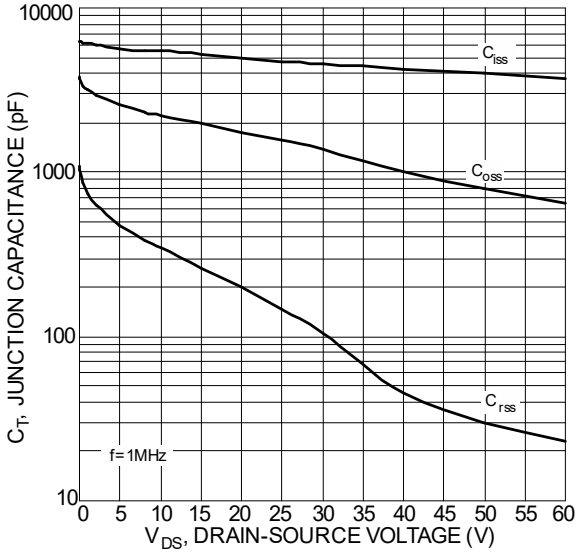


Figure 10 Typical Junction Capacitance

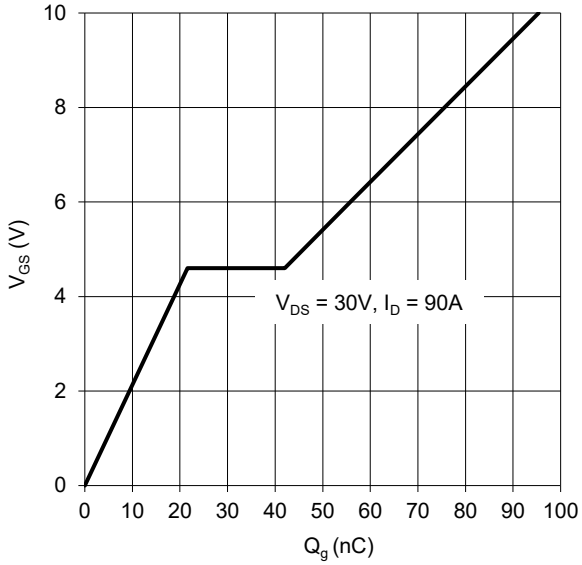


Figure 11 Gate Charge

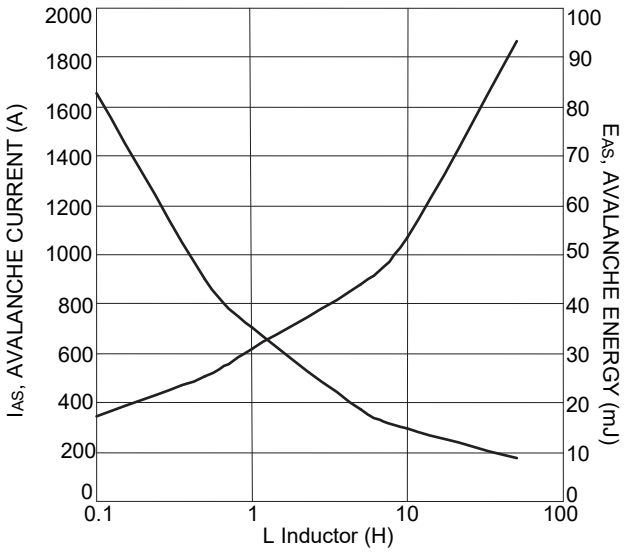


Figure 12 Single-Pulsed Avalanche Rating

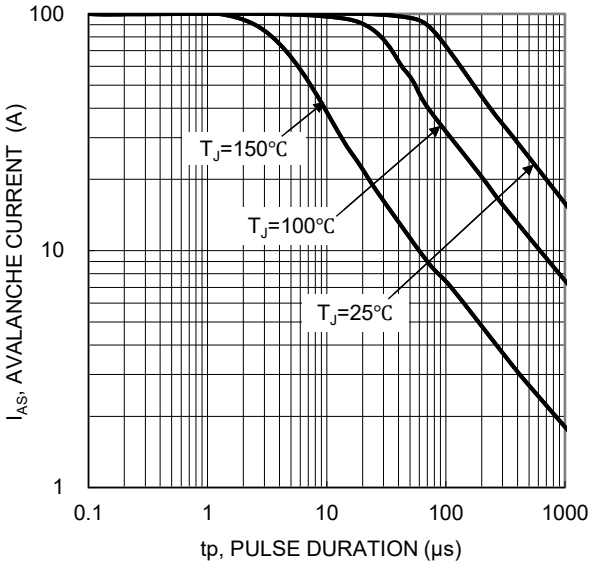


Figure 13 Avalanche Current vs. Pulse Duration

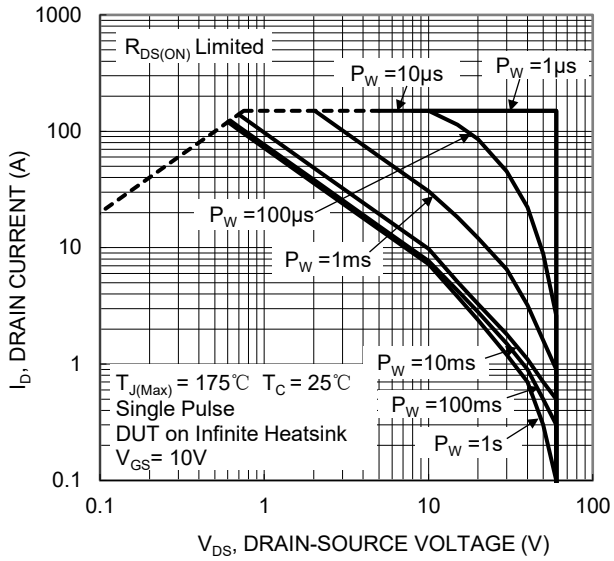


Figure 14 SOA, Safe Operation Area

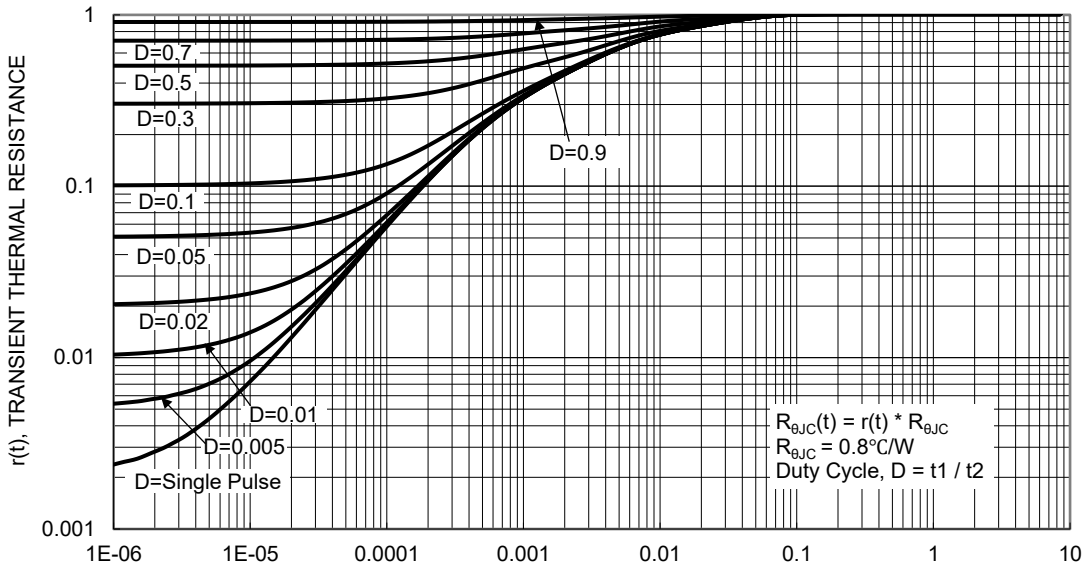
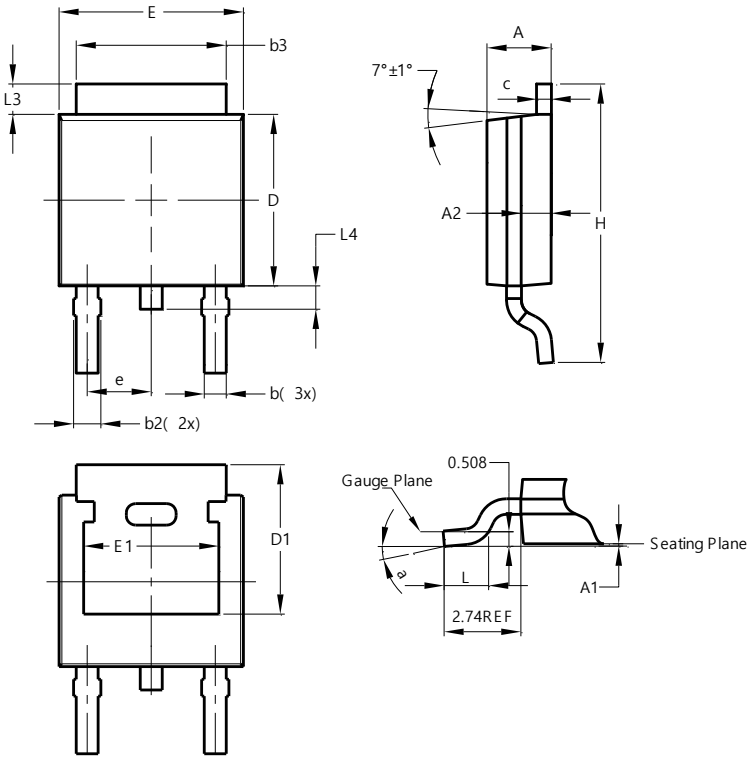


Figure 15 Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)

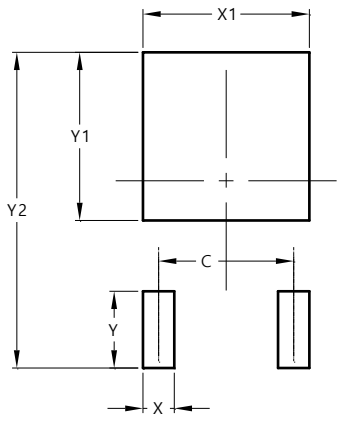


TO252 (DPAK)			
Dim	**Min**	**Max**	**Typ**
A	2.19	2.39	2.29
A1	0.00	0.13	0.08
A2	0.97	1.17	1.07
b	0.64	0.88	0.783
b2	0.76	1.14	0.95
b3	5.21	5.50	5.33
c	0.45	0.58	0.531
D	6.00	6.20	6.10
D1	5.21	--	--
e	2.286 BSC		
E	6.45	6.70	6.58
E1	4.32	--	--
H	9.40	10.41	9.91
L	1.40	1.78	1.59
L3	0.88	1.27	1.08
L4	0.64	1.02	0.83
a	0°	10°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

TO252 (DPAK)



Dimensions	Value (in mm)
C	4.572
X	1.060
X1	5.632
Y	2.600
Y1	5.700
Y2	10.700

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